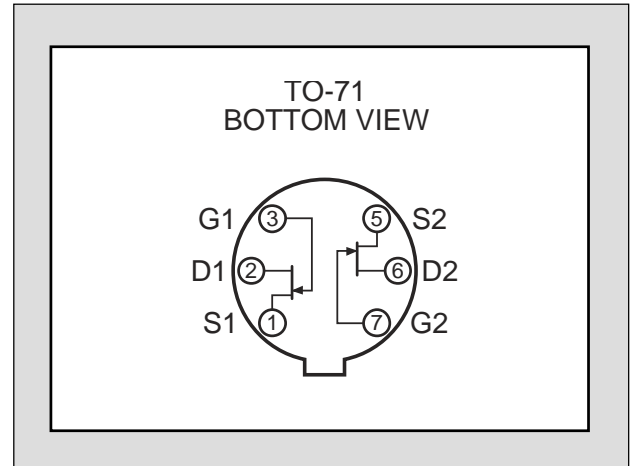


FEATURES	
SECOND SOURCE FOR SILICONIX VCR11N	
VOLTAGE CONTROLLED RESISTANCE	100 to 200 $\Omega$
<b>ABSOLUTE MAXIMUM RATINGS<sup>1</sup></b> @ 25 °C (unless otherwise stated)	
<b>Maximum Temperatures</b>	
Storage Temperature	-65 to +150 °C
Operating Junction Temperature	-55 to +135 °C
<b>Maximum Power Dissipation</b>	
Continuous Power Dissipation	300mW
<b>Maximum Current</b>	
Forward Gate Current	10mA
<b>Maximum Voltages</b>	
Gate to Drain Voltage	25V
Gate to Source Voltage	25V

# VCR11N

## N-CHANNEL JFET VOLTAGE CONTROLLED RESISTOR



\*Contact the factory for surface mount package options and pin outs.

### ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$BV_{GSS}$	Gate to Source Breakdown Voltage	-25			V	$I_G = -1\mu A, V_{DS} = 0V$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-8		-12		$I_D = 1\mu A, V_{DS} = 10V$
$I_{GSS}$	Gate Reverse Current			-0.2	nA	$V_{GS} = -15V, V_{DS} = 0V$
$r_{ds(on)}$	Dynamic Drain to Source On Resistance	100		200	$\Omega$	$V_{GS} = 0V, I_D = 0A, f = 1kHz$
$r_{DS(min)}$	Static Drain to Source On Resistance Ratio	0.95		1		$V_{DS} = 100mV, r_{DS} = 200\Omega^2$
$r_{DS(max)}$		0.95		1		$V_{GS1} = V_{GS2}, r_{DS} = 2k\Omega^2$
$C_{dgo}$	Drain to Gate Capacitance			8	pF	$V_{GD} = -10V, I_S = 0A, f = 1MHz$
$C_{sgo}$	Source to Gate Capacitance			8	pF	$V_{GS} = -10V, I_D = 0A, f = 1MHz$

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2.  $V_{GS1}$  + Control Voltage necessary to force  $r_{DS}$  to 200 $\Omega$  or 2k $\Omega$ .

Information furnished by Linear Integrated Systems is believed to be accurate and reliable. However, no responsibility is assumed for its use; nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Linear Integrated Systems.